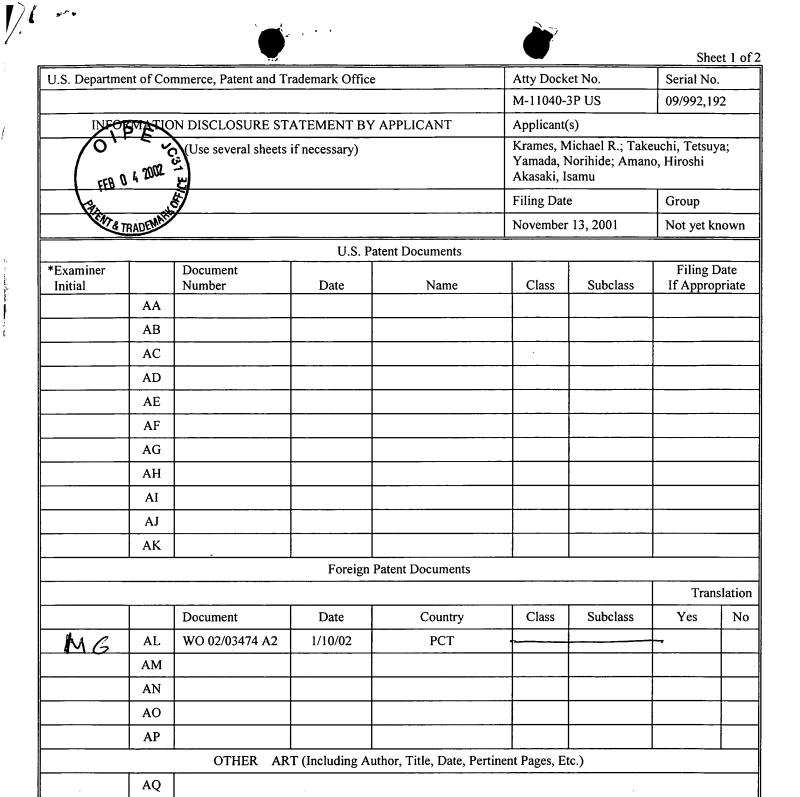
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Initial		Number	Date	Name	Class	Subclass	If Appro	priate
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